

# **isc Silicon NPN Darlington Power Transistor**

2SD1895

### **DESCRIPTION**

- · High DC Current Gain-
  - : h<sub>FE</sub>= 5000(Min)@I<sub>C</sub>= 7A
- · Low-Collector Saturation Voltage-
- : V<sub>CE(sat)</sub>= 2.5V(Max.)@I<sub>C</sub>= 7A
- Complement to Type 2SB1255
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



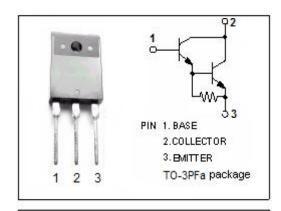
### **APPLICATIONS**

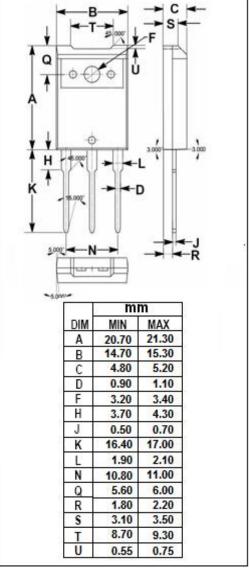
Designed for power amplifier applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)



SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	160	V	
Vceo	Collector-Emitter Voltage	140	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	Α		
Ісм	Collector Current-Peak	Α		
Pc	Collector Power Dissipation @ T <sub>C</sub> =25 ℃	100	W	
	Collector Power Dissipation @ $T_a$ =25 $^{\circ}$ C	3		
TJ	Junction Temperature	n Temperature 150		
T <sub>stg</sub>	Storage Temperature Range -55~150		$^{\circ}$	







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	140			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 7mA			2.5	٧	
$V_{\text{BE}(sat)}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 7mA			3.0	V	
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 160V; I <sub>E</sub> = 0			100	μА	
ICEO	Collector Cutoff Current	V <sub>CE</sub> = 140V; I <sub>B</sub> = 0			100	μА	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μ <b>Α</b>	
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	2000				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V	5000		30000		
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		20		MHz	
Switching Times							
ton	Turn-on Time			2.0		μs	
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 7A; I <sub>B1</sub> = I <sub>B2</sub> = 7mA, V <sub>CC</sub> = 50V		6.0		μS	
t <sub>f</sub>	Fall Time			1.2		μ <b>s</b>	

## ♦ h<sub>FE-2</sub> Classifications

Q	Р		
5000-15000	8000-30000		

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